

***Remarks***

Amendments were made to the specification to correct mistyped words and an incorrect figure element number. Also, Figure 7 was inadvertently included with the originally filed application. Figure 7 has been deleted from the application due to redundancy with Figure 1. These changes are believed to introduce no new matter, and their entry is respectfully requested.

***Conclusion***

Favorable consideration of all pending claims is respectfully solicited. If the Examiner believes, for any reason, that personal communication will expedite prosecution of this application, the Examiner is invited to telephone the undersigned at the number provided.

Respectfully submitted,

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Date: 6/3/03

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SKGF Rev. 4/9/02

**Version with markings to show changes made**

***In the Specification:***

Please amend the following paragraphs/sections as follows.

Amend paragraph 4, as follows:

The charge pump 110 outputs a signal "SCP" (charge pump signal) on the basis of the pulse signals  $\phi_R$ ,  $\phi_P$  output from the phase comparator [110] 106, to a low-pass filter (hereinafter referred to as "LPF") 112. This output signal SCP contains a pulse component in its D.C. component. The D.C. component rises and falls with the frequency changes of the pulse signals  $\phi_R$ ,  $\phi_P$ , while the pulse component changes on the basis of the phase difference of the pulse signals  $\phi_R$ ,  $\phi_P$ .

Amend paragraph 31, as follows:

A thick oxide 508 is formed on the region/substrate 504. The thick oxide 508 can comprise silicon dioxide, silicon nitride, or the like, as would be apparent to a person skilled in the semiconductor art. The thick oxide can be formed to a thickness of between about 20 and 100Å (Angstroms). The thick oxide material and specific thickness are application (e.g., depending on the applied voltage) and/or process (e.g., 0.13µm-technology) specific, as would become apparent to a person skilled in the [releveant] relevant art.

Amend paragraph 35, as follows:

The low pass filter 112 of FIG. 1 is used to filter out high frequency components of the SCP signal. According to an embodiment of the present invention, filter 112 can comprise[s] a P-gate NMOS semiconductor device 500, as described above in connection with FIG. 5. The charge pump 110 preferably accumulates electrical charge based on the difference signals and provides a voltage control signal with sufficient current to the VCO 114 to adjust phase and/or frequency of the VCO output.

Amend paragraph 36, as follows:

The PLL [is] shown in FIG. 1 is for illustrative purposes only. The present invention can be applied to a[n] PLL circuit, as well as any other circuit including a LPF.